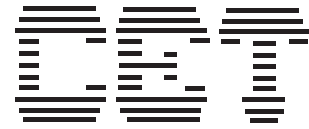


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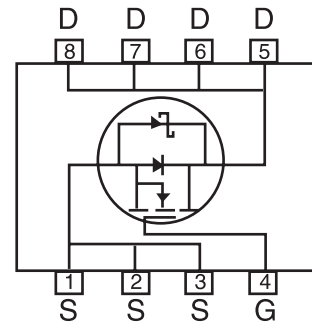
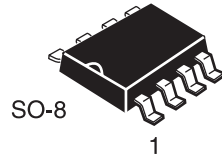


PRELIMINARY

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- 30V , 7A , $R_{DS(ON)}=28m\Omega$ @ $V_{GS}=10V$.
 $R_{DS(ON)}=42m\Omega$ @ $V_{GS}=4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Surface mount package.



ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous @ $T_J=125^{\circ}C$ -Pulsed	I_D	± 7	A
	I_{DM}	± 30	A
Drain-Source Diode Forward Current	I_S	2.3	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$

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THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^{\circ}C/W$
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			10	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A		20	28	mΩ
		V _{GS} =4.5V, I _D =3.5A		28	42	mΩ
On-State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	30			A
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =7A		16		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V f=1.0MHz		707	920	pF
Output Capacitance	C _{OSS}			355	460	pF
Reverse Transfer Capacitance	C _{RSS}			89	120	pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =25V, I _D =1A, V _{GEN} =10V, R _{GEN} =6Ω		8	15	ns
Rise Time	t _r			11	20	ns
Turn-Off Delay Time	t _{D(OFF)}			35	55	ns
Fall Time	t _f			17	28	ns
Total Gate Charge	Q _g	V _{DS} =15V, I _D =2A, V _{GS} =10V		23	29	nC
Gate-Source Charge	Q _{gs}			3		nC
Gate-Drain Charge	Q _{gd}			4		nC

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BODY DIODE & SCHOTTKY DIODE RATINGS AND CHARACTERISTICS

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Body Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 2.0A$		0.76	1.1	V
Schottky Forward Voltage	V_F	$I_F = 2A, T_C = 25^\circ C$			0.55	V
Average Forward Rectified Current	$I_{F(AV)}$				1	A

Notes

a. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

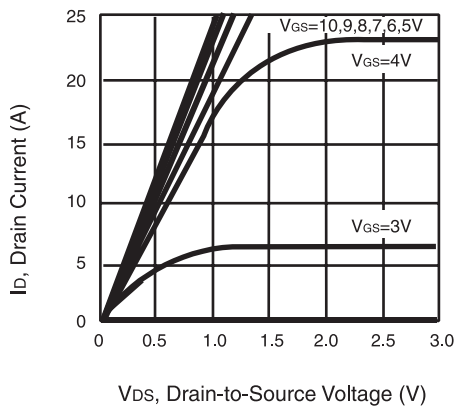


Figure 1. Output Characteristics

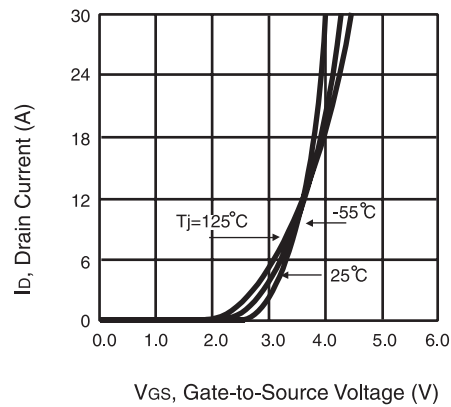


Figure 2. Transfer Characteristics

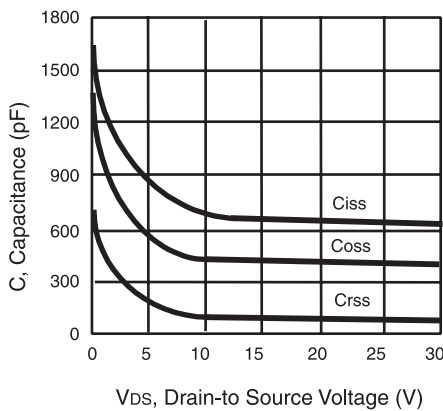


Figure 3. Capacitance

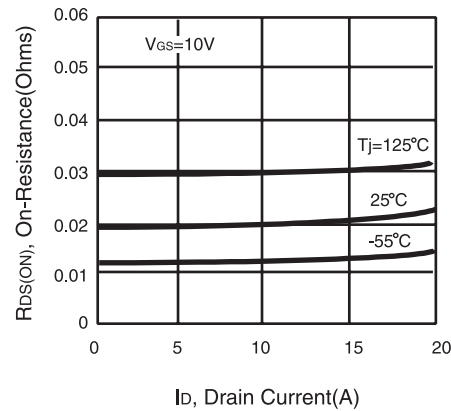


Figure 4. On-Resistance Variation with Drain Current and Temperature

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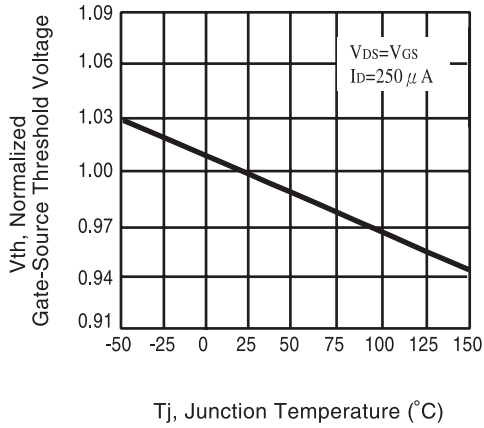


Figure 5. Gate Threshold Variation with Temperature

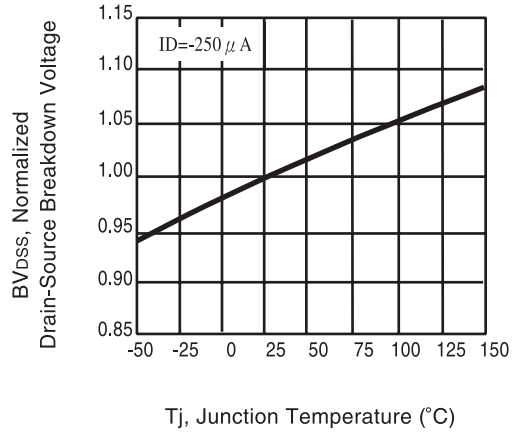


Figure 6. Breakdown Voltage Variation with Temperature

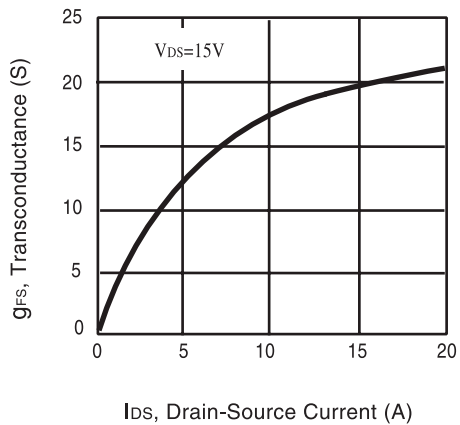


Figure 7. Transconductance Variation with Drain Current

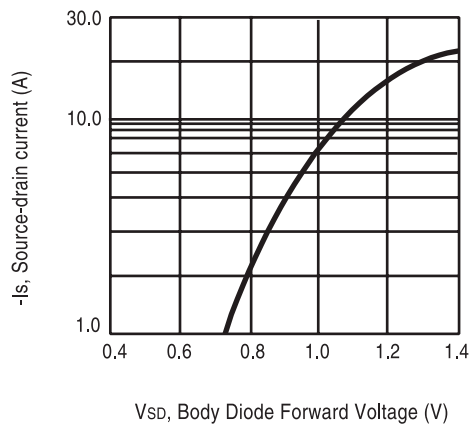


Figure 8. Body Diode Forward Voltage Variation with Source Current

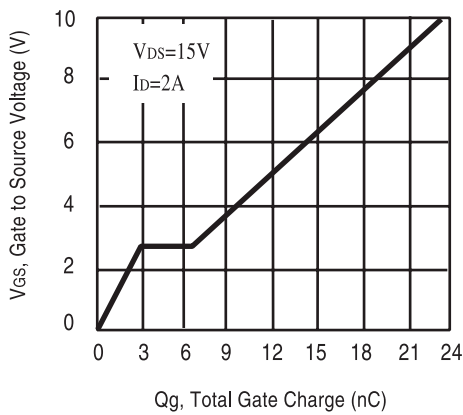


Figure 9. Gate Charge

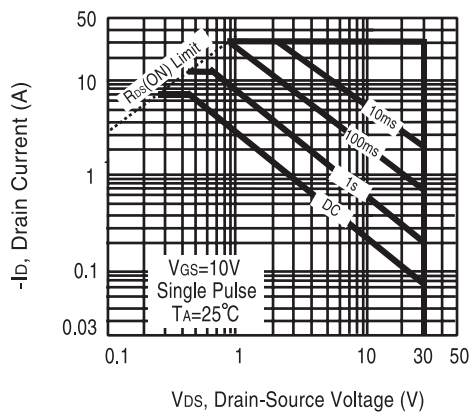


Figure 10. Maximum Safe Operating Area

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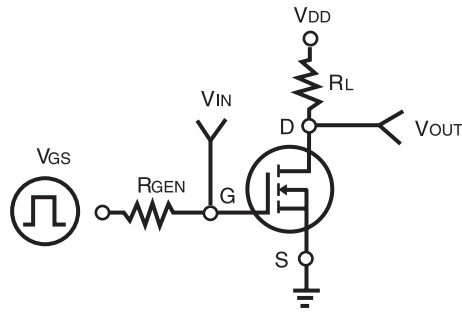


Figure 11. Switching Test Circuit

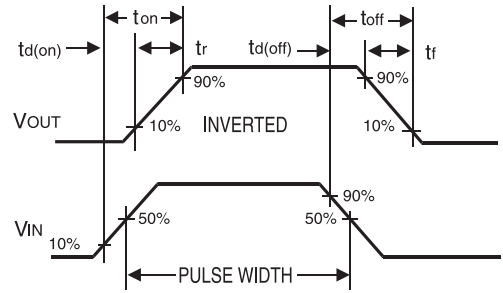


Figure 12. Switching Waveforms

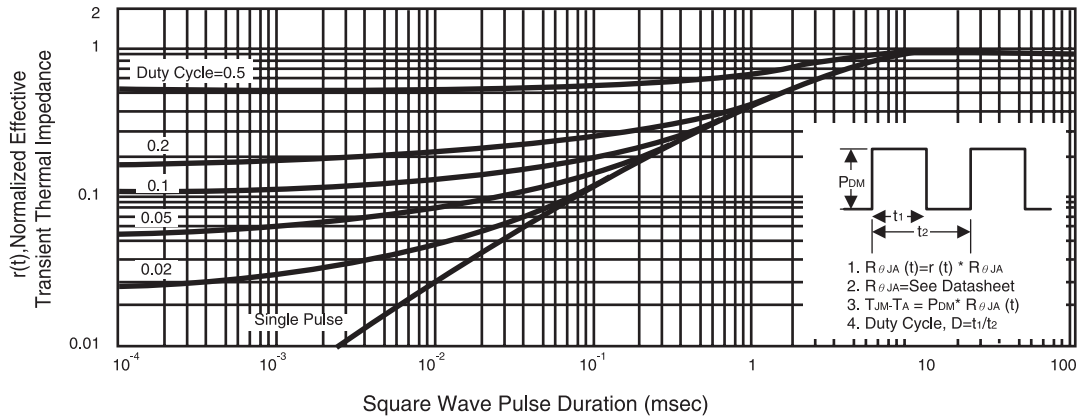


Figure 13. Normalized Thermal Transient Impedance Curve